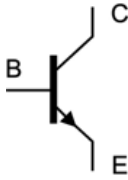


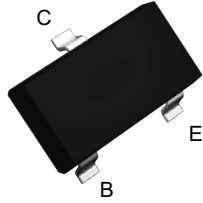
GSBC817W Series NPN Transistors

Feature

- Epoxy meets UL 94V-0 flammability rating
- Small outline surface mount package
- Low current leakage
- For high-speed switching applications



Schematic Diagram



SOT-323

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current-Continuous	I _C	500	mA
Collector Power Dissipation	P _C	200	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 To +150	°C

h_{FE(1)} Classifications

Rank	GSBC817-16W	GSBC817-25W	GSBC817-40W
Range	100-250	160-400	250-600
Marking	6A	6B	6C

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	50	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	45	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1\mu\text{A}, I_C=0$	5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$	-	-	0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	100	-	600	-
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=500\text{mA}$	40	-	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	-	1.2	V
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE}=1\text{V}, I_C=500\text{mA}$	-	-	1.2	V
Transition Frequency	f_T	$V_{CE}=5\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100	-	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$	-	-	10	pF

Typical Characteristic Curves

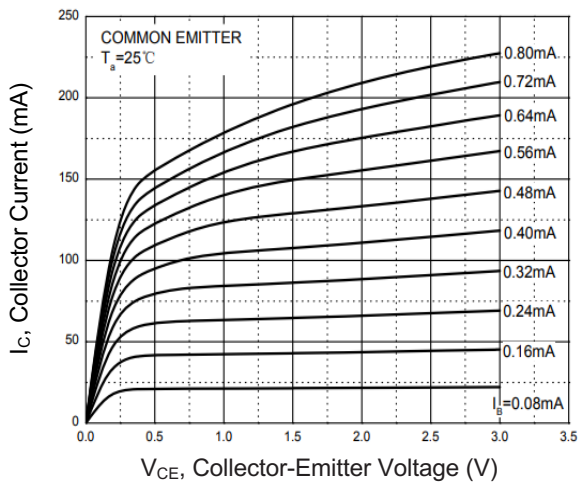


Figure 1. Static Characteristics

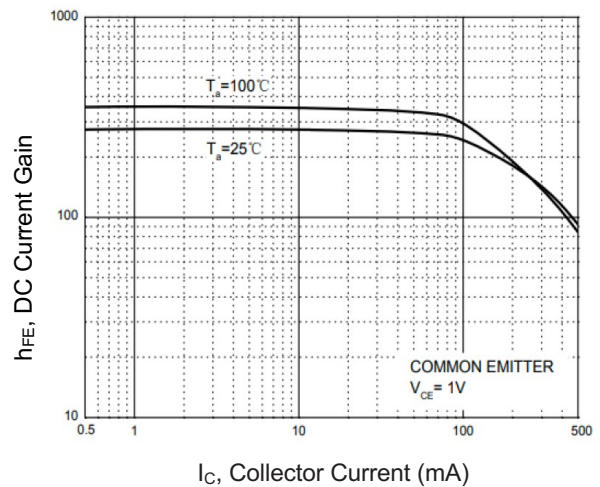


Figure 2. DC Current Gain

Typical Characteristic Curves

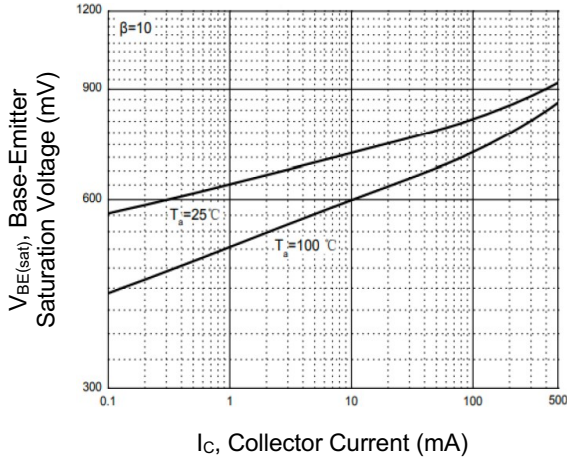


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

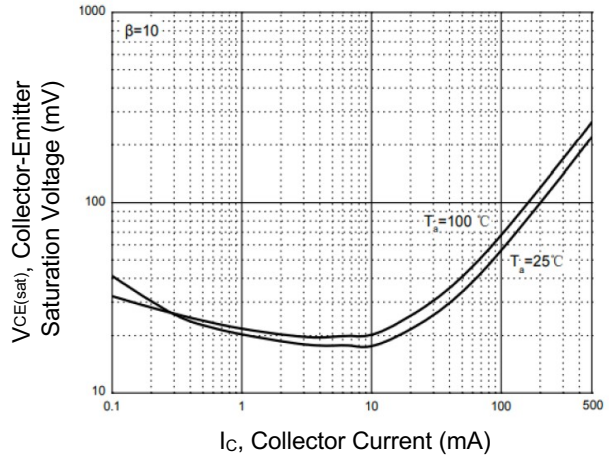


Figure 4. Collector-Emitter Saturation Voltage vs. Collector Current

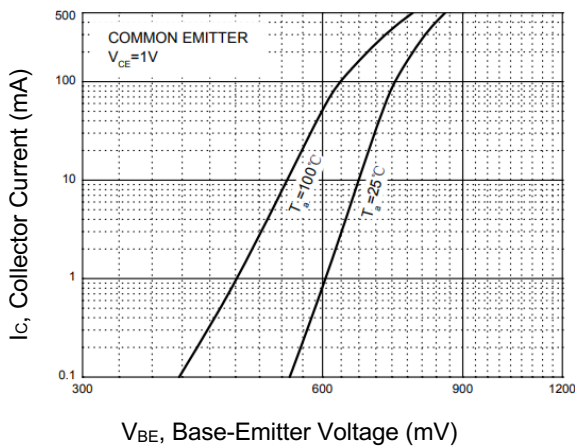


Figure 5. Collector Current vs. Base-Emitter Voltage

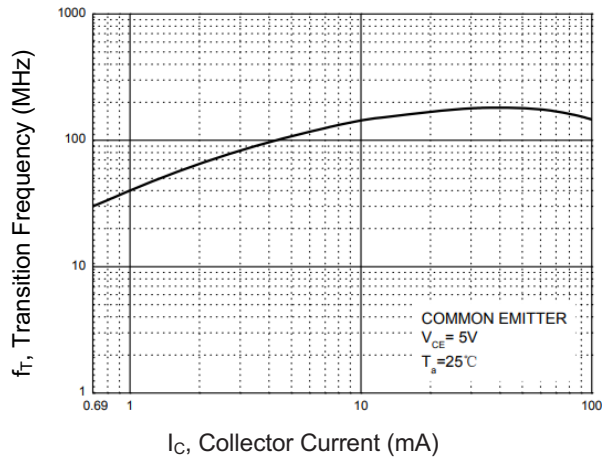


Figure 6. Transition Frequency vs. Collector Current

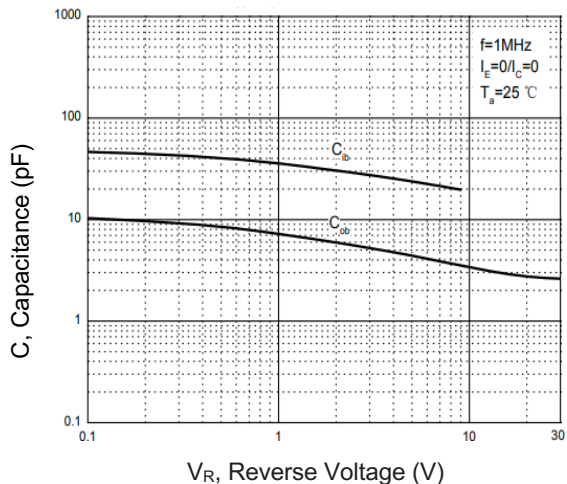


Figure 7. Capacitance Characteristics

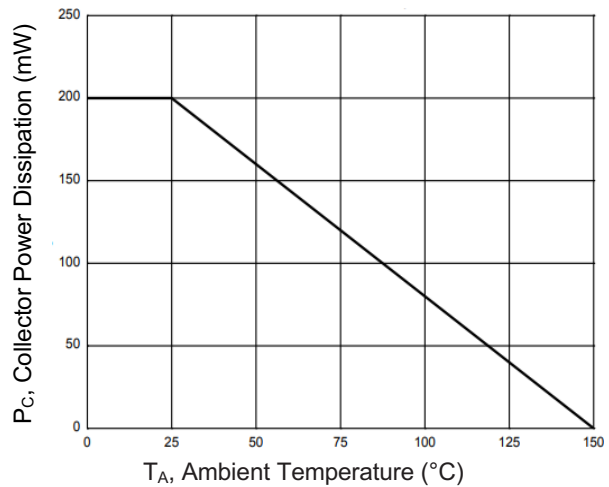
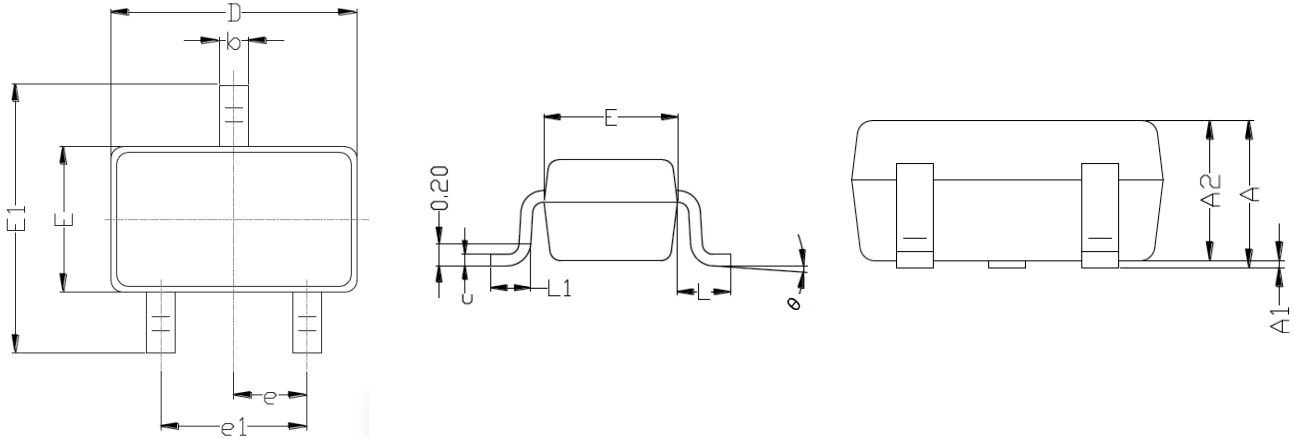


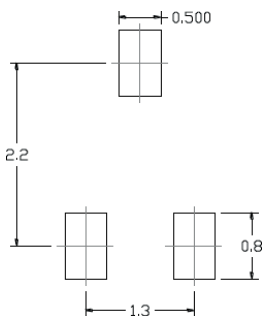
Figure 8. Power Derating

Package Outline Dimensions (SOT-323)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.00	0.035	0.039
A1	0.00	0.10	0.000	0.004
A2	0.90	1.00	0.035	0.039
b	0.20	0.40	0.008	0.016
c	0.08	0.15	0.003	0.006
D	2.00	2.20	0.079	0.087
E	1.15	1.35	0.045	0.053
E1	2.15	2.45	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.20	1.40	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.26	0.46	0.010	0.018
θ	0°	8°	0°	8°

Recommended Pad Layout



Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

Order Information

Device	Package	Carrier	Quantity
GSBC817W Series	SOT-323	Tape & Reel	3,000 Pcs / Reel

For more information, please contact us at: inquiry@goodarksemi.com